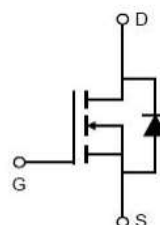




1. Description

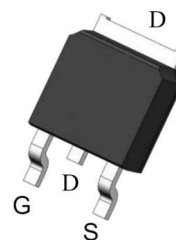
SS18N10DSL, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

Schematic Diagram



KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	100	V
I_D	45	A
$R_{DS(on).typ}$	16	mΩ



TO-252

FEATURES:

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 18m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS:

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS18N10DSL	TO-252	SS18N10DSL	Reel